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Question Paper



## MANIPAL ACADEMY OF HIGHER EDUCATION

B.Tech Ist Semester Sessional Examination September 2024

### BASIC ELECTRONICS [ECE 1071]

**Marks: 30**

**Duration: 90 mins.**

#### MCQ

**Answer all the questions.**

Section Duration: 20 mins

- 1) At 300 K, for a diode current of 1mA, a certain germanium diode requires a forward bias of 0.1435 V, whereas a certain silicon diode requires a forward bias of 0.718 V. Under the condition stated above, the closest approximation of the ratio of reverse saturation current in germanium diode to that in silicon diode is (1)

1    5     $4 \times 10^3$      $8 \times 10^3$

- 2) A full wave rectifier has a load of  $1\text{ k}\Omega$ , the AC voltage applied to the diode is (200-0-200) V. If diode resistance is neglected, the value of average current is (1)

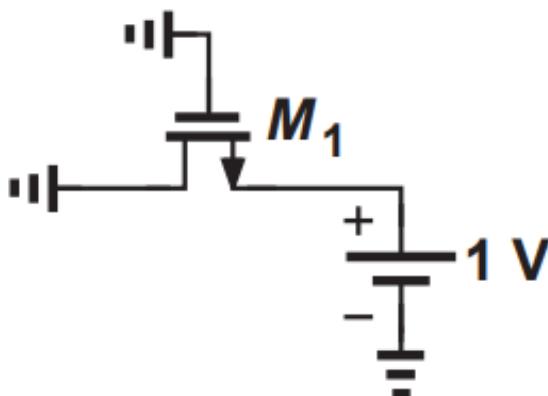
0.18 A    0.16 A    0.56 A    0.36 A

- 3) The photodiodes are operated in

<u>Reverse bias condition</u>	<u>Zero bias condition</u>	<u>Either of the two options mentioned in (a) and (b)</u>	<u>None of the two options mentioned in (a) and (b)</u>	(1)
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- 4) In a non-inverting OPAMP amplifier, when the feedback resistance equals the resistance connected from the inverting input to ground, the closed loop gain is (1)

- 5) Find the region of operation of M1 shown in figure, if  $V_{Th} = 0.4V$



(1)

Cut-off region    Trode region    Saturation region    Deep Trode region

#### DESCRIPTIVE

**Answer all the questions.**

- 6) Derive the Drain Current Equation for an n-channel MOSFET. If the drain-to-source voltage for an N channel MOSFET  $V_{DS}=0.8V$ . Assuming

$$V_{th}=1.0 \text{ V}, V_{GS}=3.0 \text{ V} \text{ and } \frac{1}{2} \mu_n C_{ox} \frac{W}{L} = 150 \mu A/V^2 \quad (4)$$

Identify the region of operation of the MOSFET and Calculate the drain current  $I_D$

- 7) Explain the two primary mechanisms of diode breakdown. Discuss the impact of temperature on these mechanisms and the overall diode breakdown voltage. (3)

- 8) A Silicon diode at room temperature ( $27^\circ\text{C}$ ) with a saturation current of  $10\text{pA}$  has a forward current of  $20.4 \text{ mA}$ . Find the voltage applied across the diode. Take  $\eta=2$  for silicon. (3)

- 9) A half wave rectifier with capacitor filter is supplied from transformer having peak secondary voltage  $20 \text{ V}$  and frequency  $50 \text{ Hz}$ . The load resistance is  $560 \Omega$  and capacitor used is  $1000 \mu\text{F}$ . Calculate ripple factor and dc output voltage. Also draw the circuit of half wave rectifier with capacitive filter (3)

- 10) A  $50 \text{ V}$  dc power supply is connected through a series resistance of  $1 \text{ k}\Omega$

to the regulator circuit. The parameters of the Zener diode used are  $V_Z = 10$  V with  $I_{Z\min} = 1$  mA and power rating  $P_{Z\max} = 200$  mW. Calculate the proper range of load resistor  $R_L$  to maintain regulation. (3)

- 11) For an OPAMP, when  $V_1$  is 150 mV and  $V_2$  is 145 mV, output voltage is 8 V. For the same OPAMP, when  $V_1 = V_2 = 1$  mV, output voltage is 12 mV. Calculate the CMRR of the OPAMP in dB (3)
- 12) A centre-tapped FWR is supplied with 220 V, 50 Hz, AC mains through a step-down transformer with turns ratio equal to 5:1. If  $R_L = 500 \Omega$ , find the average and RMS value of the load current, PIV rating of the diode used for proper working. (2)
- 13) With the neat circuit diagram, explain the working of full wave bridge rectifier. Derive the expressions for Average/DC value of load current and RMS value of load current. (2)
- 14) Derive the expression for output voltage ( $V_{out}$ ) for the figure shown below. Calculate the output voltage for the given DC input voltage.

